In the Claims

The pending claims are listed below.

1-5. (canceled)

6. (previously presented) A method of manufacturing a semiconductor device which comprises a first semiconductor region of a first conductivity type with a first connection conductor forming a collector region of a bipolar transistor, a second semiconductor region of a second conductivity type opposed to the first conductivity type with a second connection conductor forming a base region of the transistor, and a third semiconductor region of the first conductivity type with a third connection conductor forming an emitter region of the transistor; said method comprising:

forming the first semiconductor region of the first conductivity type;

forming the second semiconductor region on the first semiconductor region, the second semiconductor region having a partial region with a smaller flux of dopant atoms than another part of the second semiconductor region;

forming the third semiconductor region which lies recessed in the other part, and outside the partial region, of the second semiconductor region; and

providing first, second and third connection conductors to the first, second and third regions with a connection conductor respectively, wherein the second conductor is exclusively connected to the second semiconductor region and is adjacent to the partial region of the second semiconductor region.

7. (previously presented) A method as claimed in claim 6, characterized in that the partial region of the second semiconductor region is formed below the second connection conductor and is given a smaller thickness and a lower doping concentration than those in the other region.

8. (previously presented) A method as claimed in claim 6, characterized in that the partial region of the second semiconductor region is given a smaller thickness than that in the other region.

9. (previously presented) A method as claimed in claim 6, characterized in that the partial region of the second semiconductor region is formed by means of ion implantation.

10-20. (canceled)